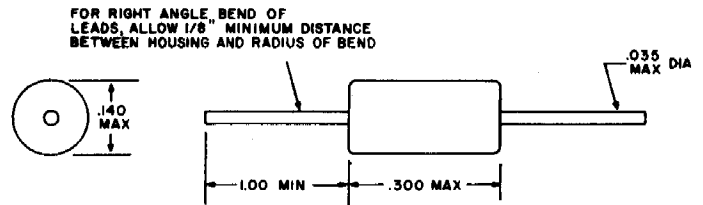
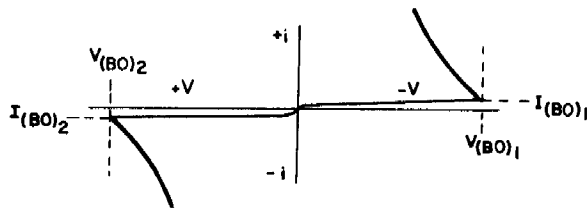


Diac

Silicon Bidirectional Trigger

The Diac is a diffused silicon bi-directional trigger diode which may be used to trigger the TRIAC or Silicon Controlled Rectifiers. The device has a three-layer structure having negative resistance switching characteristics for both directions of applied voltage.

VOLT - AMPERE CHARACTERISTICS

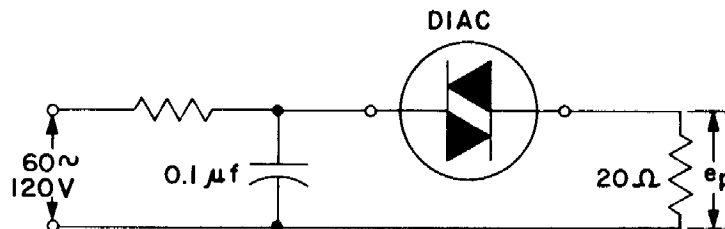


Storage Temperature.....  $T_{STG}$   $-40^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$   
 Operating Temperature.....  $T_J$   $-40^{\circ}\text{C}$  to  $+100^{\circ}\text{C}$

MAXIMUM RATINGS at  $50^{\circ}\text{C}$  Ambient

Peak Current (10  $\mu\text{sec}$  duration, 120 cycle repetition rate).....  $I_p$   $\pm 2$  Amperes Max.  
 Peak Output Voltage\*.....  $e_p$   $\pm 3$  Volts Min.

\*CIRCUIT FOR PEAK OUTPUT VOLTAGE TEST



CHARACTERISTICS at  $25^{\circ}\text{C}$  Ambient

Test	Symbols	Min.	Typ.	Max.	Units
Breakover Voltage	$V(BR)_1$ and $V(BR)_2$	28	32	36	Volts
Breakover Voltage Temp. Coefficient		-	0.1	-	%/ $^{\circ}\text{C}$
Breakover Currents	$I(BR)_1$ and $I(BR)_2$	-	-	200	$\mu\text{amp}$
Breakover Voltage Symmetry	$ V(BR)_1  -  V(BR)_2 $	-	-	3.8	Volts

